

Silicon PNP Power Transistors

2N6049

DESCRIPTION

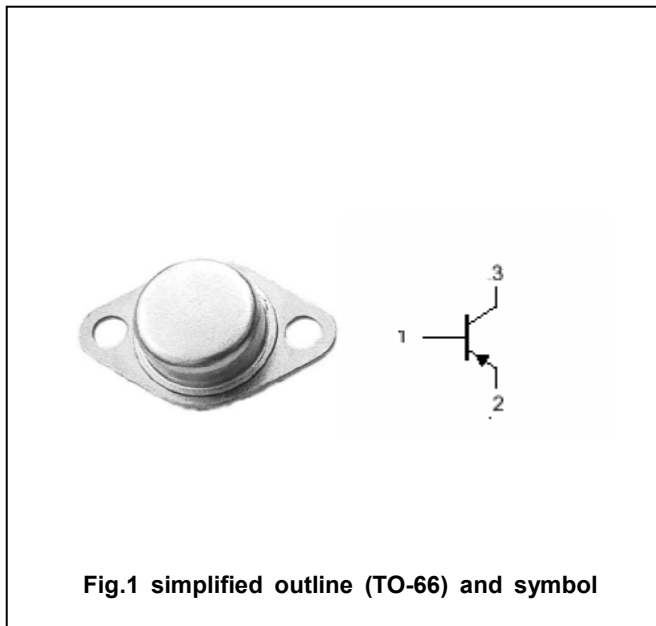
- With TO-66 package
- Complement to type 2N3054A

APPLICATIONS

- Designed for general purpose switching and amplifier applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-90	V
V _{CEO}	Collector-emitter voltage	Open base	-55	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-4	A
I _{CM}	Collector current-peak		-10	A
I _B	Base current		-2	A
P _D	Power dissipation	T _C =25°C	75	W
T _j	Junction temperature		200	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	2.33	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-0.1A ; I _B =0	-55			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-0.5A ; I _B =-50mA			-0.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.8A			-2.0	V
V _{BE}	Base -emitter on voltage	I _C =-0.5A ; V _{CE} =-4V			-1.0	V
I _{CEX}	Collector cut-off current	V _{CE} =-90V; V _{BE(off)} =-1.5V T _C =150°C			-1.0 -6.0	mA
I _{CEO}	Collector cut-off current	V _{CE} =-30V; I _B =0			-0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain	I _C =-0.5A ; V _{CE} =-4V	25		100	
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-4V	6			
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-10V, f=0.1MHz			200	pF
f _T	Transition frequency	I _C =-0.2A ; V _{CE} =-10V; f=1MHz	3.0			

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PACKAGE OUTLINE

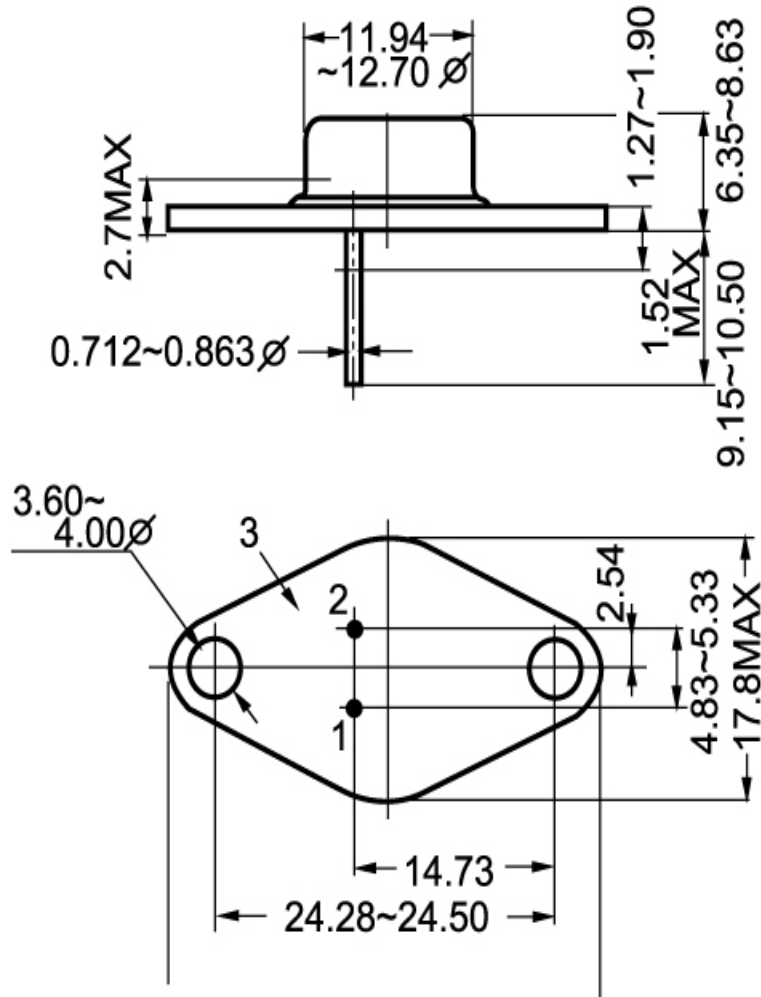


Fig.2 Outline dimensions